

## TENTATIVE

### Features

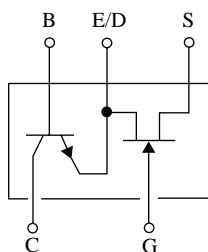
- Composite type with an J-FET transistor and a PNP transistor contained in the conventional CP package, improving the mounting efficiency greatly.
- The FC22 is formed with two chips, one being equivalent to the 2SC4639 and the other the 2SK3266, placed in one package.
- Drain and emitter are shared.

### Absolute Maximum Ratings / Ta=25°C

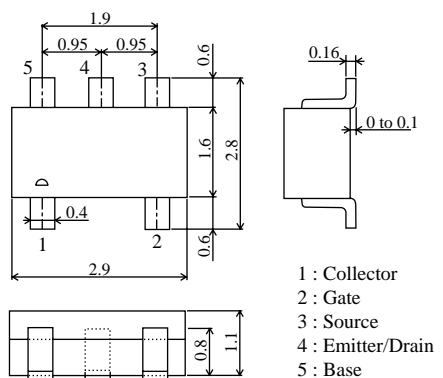
			unit
<b>[FET]</b>			
Drain - to - Source Voltage	VDSX	15	V
Gate - to - Drain Voltage	VGDS	- 15	V
Gate Current	IG	10	mA
Drain Current	ID	50	mA
Allowable Power Dissipation	PD	200	mW
<b>[TR]</b>			
Collector - to - Base Voltage	VGBO	55	V
Collector - to - Emitter Voltage	VCEO	50	V
Emitter - to - Base Voltage	VEBO	6	V
Collector Current	IC	150	mA
Collector Current(Pulse)	ICP	300	mA
Base Current	IB	30	mA
Collector Dissipation	PC	200	mW
<b>[Common Ratings]</b>			
Total Dissipation	PT	300	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	- 55 to +150	°C

Continued on next page.

### Electrical Connection



### Package Dimensions 2122 (unit : mm)



- 1 : Collector
  - 2 : Gate
  - 3 : Source
  - 4 : Emitter/Drain
  - 5 : Base
- SANYO : CP5

Specifications and information herein are subject to change without notice.

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## FC22

Continued from preceding page.

### Electrical Characteristics at Ta=25°C

[FET]			min	typ	max	unit
G-D Breakdown Voltage	V(BR)GDS	IG=-10μA, VDS=0	-15			V
Gate Cutoff Current	IGSS	VGS=-10V, VDS=0			-1.0	nA
G-S Cutoff Voltage	VGS(OFF)	VDS=5V, ID=100μA	-0.3	-0.7	-1.5	V
Drain Current	IDSS	VDS=5V, VGS=0	6.0*		32.0*	mA
Forward Transfer Admittance	yfs	VDS=5V, VGS=0, f=1kHz	20	33		mS
Input Capacitance	Ciss	VDS=5V, VGS=0, f=1MHz		10.0		pF
Reverse Transfer Capacitance	Crss	VDS=5V, VGS=0, f=1MHz		2.9		pF
Noise Figure	NF	VDS=5V, Rg=1kΩ, ID=1mA, f=1kHz		1.0		dB

[TR]						
Collector Cutoff Current	ICBO	VCB=35V, IE=0			0.1	μA
Emitter Cutoff Current	IEBO	VEB=4V, IC=0			0.1	μA
DC Current Gain	hFE	VCE=6V, IC=1mA	135		400	
Gain-Bandwidth Product	fT	VCE=6V, IC=10mA		200		MHz
Output Capacitance	Cob	VCB=6V, f=1MHz		1.7		pF
C-E Saturation Voltage	VCE(sat)	IC=50mA, IB=5mA		0.08	0.4	V
B-E Saturation Voltage	VBE(sat)	IC=50mA, IB=5mA		0.8	1.0	V
C-B Breakdown Voltage	V(BR)CBO	IC=10μA, IE=0	55			V
C-E Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	50			V
E-B Breakdown Voltage	V(BR)EBO	IE=10μA, IC=0	6			V
Turn-On Time	ton	See specified Test Circuit.		0.15		μs
Storage Time	tstg	"		0.75		μs
Fall Time	tf	"		0.20		μs

\* : The FC22 is classified by IDSS as follows : (unit : mA)

6.0	F	12.0	10.0	G	20.0	16.0	H	32.0
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IDSS rank : F, G, H

The specifications shown above are for each individual FET or transistor.

### Switching Time Test Circuit

